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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	90
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg890f256-bga112t

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.28 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG890 to keep track of time and retain data, even if the main power source should drain out.

2.1.29 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.30 General Purpose Input/Output (GPIO)

In the EFM32WG890, there are 90 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.1.31 Liquid Crystal Display Driver (LCD)

The LCD driver is capable of driving a segmented LCD display with up to 8x36 segments. A voltage boost function enables it to provide the LCD display with higher voltage than the supply voltage for the device. In addition, an animation feature can run custom animations on the LCD display without any CPU intervention. The LCD driver can also remain active even in Energy Mode 2 and provides a Frame Counter interrupt that can wake-up the device on a regular basis for updating data.

2.2 Configuration Summary

The features of the EFM32WG890 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA

Table 2.1. Col	figuration Summary
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3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB} =25°C and V_{DD} =3.0 V, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Symbol	Parameter	Condition	Min	Тур	Max	Unit
T _{STG}	Storage tempera- ture range		-40		150 ¹	°C
Τ _S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V _{DDMAX}	External main sup- ply voltage		0		3.8	V
V _{IOPIN}	Voltage on any I/O pin		-0.3		V _{DD} +0.3	V

Table 3.1. Absolute Maximum Ratings

¹Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Тур	Max	Unit
T _{AMB}	Ambient temperature range	-40		85	°C
V _{DDOP}	Operating supply voltage	1.98		3.8	V
f _{APB}	Internal APB clock frequency			48	MHz
f _{AHB}	Internal AHB clock frequency			48	MHz

3.8 General Purpose Input Output

Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOIL}		Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
V	Output high volt- age (Production test	Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
VIOOH	condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
		Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
V _{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE =	Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
	STANDARD)	Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V

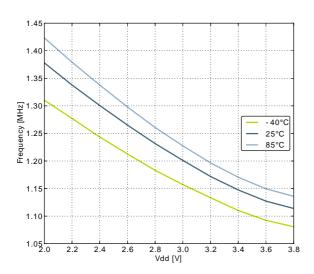
3.9.4 HFRCO

Table 3.12. HFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
f	Oscillation frequen-	14 MHz frequency band	13.7	14.0	14.3	MHz
f _{HFRCO}	cy, V _{DD} = 3.0 V, T _{AMB} =25°C	11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
t _{HFRCO_settling}	Settling time after start-up	f _{HFRCO} = 14 MHz		0.6		Cycles
		f _{HFRCO} = 28 MHz		165	215	μA
		f _{HFRCO} = 21 MHz		134	175	μA
1	Current consump-	f _{HFRCO} = 14 MHz		106	140	μA
I _{HFRCO}	tion	f _{HFRCO} = 11 MHz		94	125	μA
		f _{HFRCO} = 6.6 MHz		77	105	μA
		f _{HFRCO} = 1.2 MHz		25	40	μA
DC _{HFRCO}	Duty cycle	f _{HFRCO} = 14 MHz	48.5	50	51	%
TUNESTEP _{H-} FRCO	Frequency step for LSB change in TUNING value			0.3 ¹		%

¹The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.18. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature



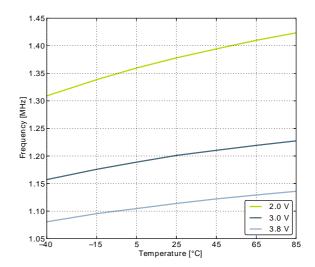


Figure 3.19. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

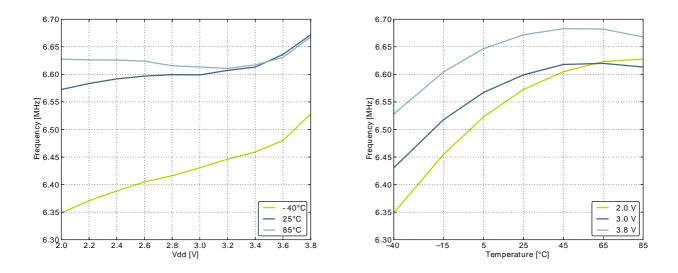


Figure 3.20. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

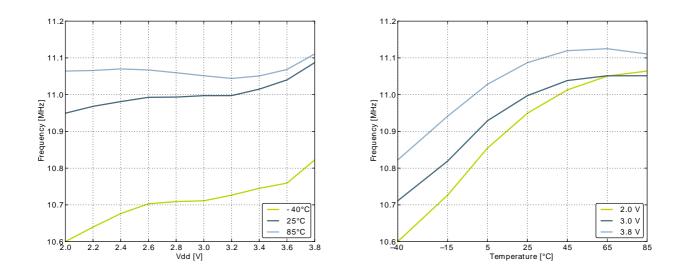
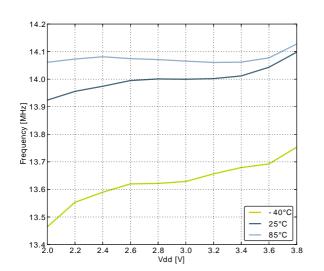
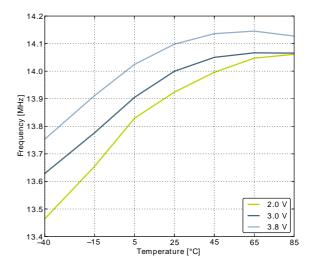


Figure 3.21. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature





3.9.5 AUXHFRCO

Table 3.13. AUXHFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
f	Oscillation frequen-	14 MHz frequency band	13.7	14.0	14.3	MHz
[†] AUXHFRCO	cy, V _{DD} = 3.0 V, T _{AMB} =25°C	11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
t _{AUXHFRCO_settlir}	_g Settling time after start-up	f _{AUXHFRCO} = 14 MHz		0.6		Cycles
DC _{AUXHFRCO}	Duty cycle	f _{AUXHFRCO} = 14 MHz	48.5	50	51	%
TUNESTEP _{AUX} HFRCO	Frequency step for LSB change in TUNING value			0.3 ¹		%

¹The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

Table 3.14. ULFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{ULFRCO}	Oscillation frequen- cy	25°C, 3V	0.7		1.75	kHz
TC _{ULFRCO}	Temperature coeffi- cient			0.05		%/°C
VC _{ULFRCO}	Supply voltage co- efficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

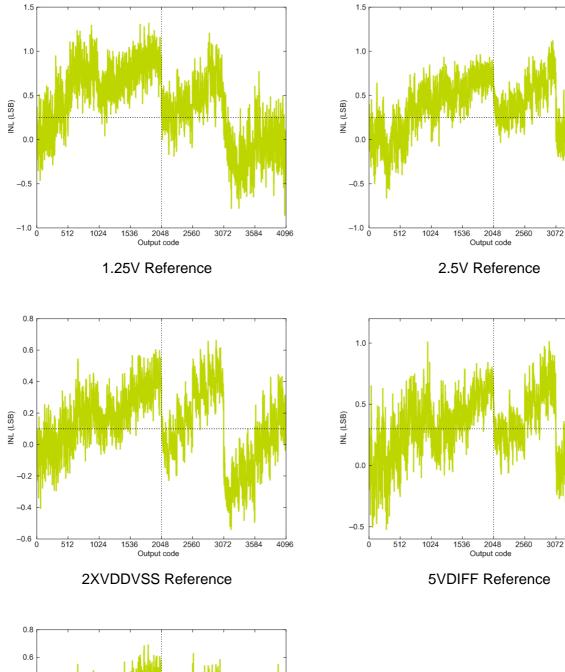
Table 3.15. ADC

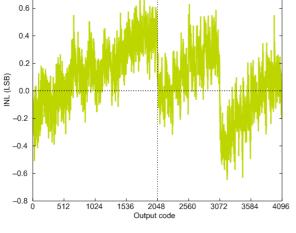
Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ADCIN}	Input voltage range	Single ended	0		V _{REF}	V
V ADCIN	input voltage range	Differential	-V _{REF} /2		V _{REF} /2	V
VADCREFIN	Input range of exter- nal reference volt- age, single ended and differential		1.25		V _{DD}	V
V _{ADCREFIN_CH7}	Input range of ex- ternal negative ref- erence voltage on channel 7	See V _{ADCREFIN}	0		V _{DD} - 1.1	V
V _{ADCREFIN_CH6}	Input range of ex- ternal positive ref-	See V _{ADCREFIN}	0.625		V _{DD}	V



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
	and ADC core in NORMAL mode					
	Startup time of ref- erence generator and ADC core in KEEPADCWARM mode			1		μs
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
	Signal to Noise Ra- tio (SNR)	1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
SNR _{ADC}		1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		69		dB
SNRADC		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, V _{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		70		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB
SINAD _{ADC}	SIgnal-to-Noise And Distortion-ratio	1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
	(SINAD)	1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB

Figure 3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C





VDD Reference

3584

3584

4096

4096



Figure 3.29. ADC Absolute Offset, Common Mode = Vdd /2

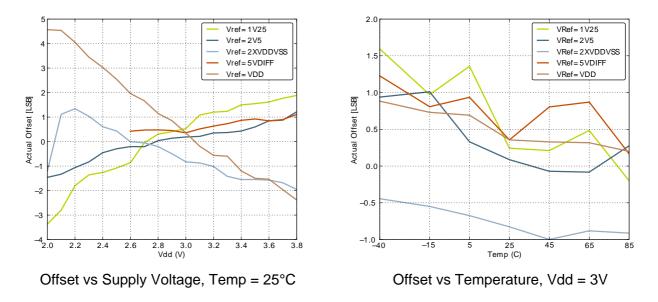


Figure 3.30. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V

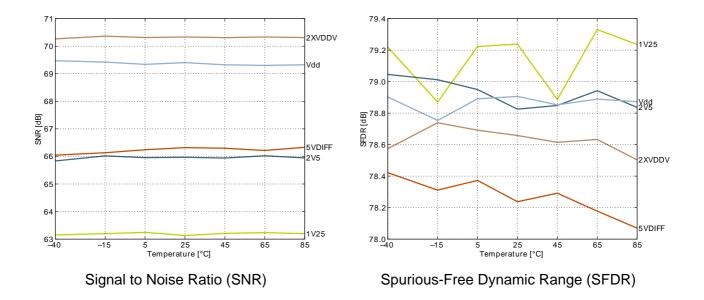




Figure 3.34. OPAMP Negative Power Supply Rejection Ratio

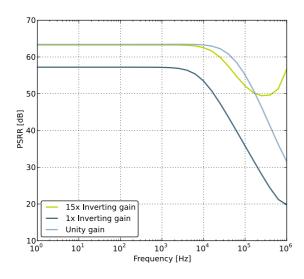


Figure 3.35. OPAMP Voltage Noise Spectral Density (Unity Gain) Vout=1V

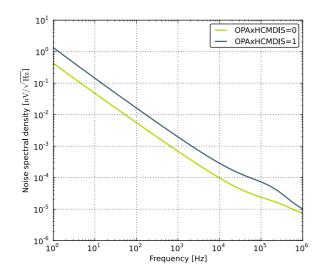
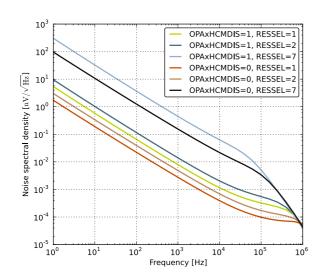


Figure 3.36. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)



3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ACMPIN}	Input voltage range		0		V _{DD}	V
V _{ACMPCM}	ACMP Common Mode voltage range		0		V _{DD}	V
		BIASPROG=0b0000, FULL- BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	μA
I _{ACMP}	Active current	BIASPROG=0b1111, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	μΑ
		BIASPROG=0b1111, FULL- BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	μΑ
I _{ACMPREF}	Current consump- tion of internal volt- age reference	Internal voltage reference off. Using external voltage refer- ence		0		μΑ
		Internal voltage reference		5		μA
V _{ACMPOFFSET}	Offset voltage	BIASPROG= 0b1010, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
V _{ACMPHYST}	ACMP hysteresis	Programmable		17		mV
		CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
D	Capacitive Sense	CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
R _{CSRES}	Internal Resistance	CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
t _{ACMPSTART}	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 47). $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

 $I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF}$

(3.1)

3.14 Voltage Comparator (VCMP)

Table 3.19. VCMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{VCMPIN}	Input voltage range			V _{DD}		V
V _{VCMPCM}	VCMP Common Mode voltage range			V _{DD}		V
	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	μA
IVCMP	Active current	BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	35	μA
t _{VCMPREF}	Startup time refer- ence generator	NORMAL		10		μs
M	Offect veltage	Single ended		10		mV
V _{VCMPOFFSET}	Offset voltage	Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			61	210	mV
t _{VCMPSTART}	Startup time				10	μs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

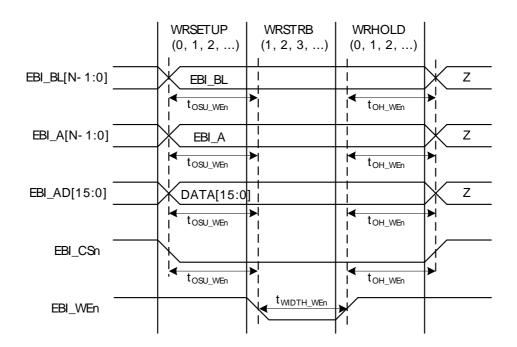
VCMP Trigger Level as a Function of Level Setting

V_{DD Trigger Level}=1.667V+0.034 ×TRIGLEVEL

(3.2)

3.15 EBI

Figure 3.38. EBI Write Enable Timing





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Symbol	Parameter	Min	Тур	Мах	Unit
t _{H_ARDY} ^{1 2 3 4}	Hold time, from trailing EBI_REn, EBI_WEn edge to EBI_ARDY invalid	-1 + (3 * t _{HFCORECLK})			ns

¹Applies for all addressing modes (figure only shows D16A8.)

²Applies for EBI_REn, EBI_WEn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

 $^4\text{Measurement}$ done at 10% and 90% of V_{DD} (figure shows 50% of $_{\text{VDD}})$

3.16 LCD

Table 3.25. LCD

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LCDFR}	Frame rate		30		200	Hz
NUM _{SEG}	Number of seg- ments supported			36×8		seg
V _{LCD}	LCD supply voltage range	Internal boost circuit enabled	2.0		3.8	V
I _{LCD}		Display disconnected, stat- ic mode, framerate 32 Hz, all segments on.		250		nA
	Steady state current consumption.	Display disconnected, quadru- plex mode, framerate 32 Hz, all segments on, bias mode to ONETHIRD in LCD_DISPCTRL register.		550		nA
I _{LCDBOOST}	Steady state Cur- rent contribution of internal boost.	Internal voltage boost off		0		μA
		Internal voltage boost on, boosting from 2.2 V to 3.0 V.		8.4		μA
		VBLEV of LCD_DISPCTRL register to LEVEL0		3.02		V
		VBLEV of LCD_DISPCTRL register to LEVEL1		3.15		V
		VBLEV of LCD_DISPCTRL register to LEVEL2		3.28		V
		VBLEV of LCD_DISPCTRL register to LEVEL3		3.41		V
V _{BOOST}	Boost Voltage	VBLEV of LCD_DISPCTRL register to LEVEL4		3.54		V
		VBLEV of LCD_DISPCTRL register to LEVEL5		3.67		V
		VBLEV of LCD_DISPCTRL register to LEVEL6		3.73		V
		VBLEV of LCD_DISPCTRL register to LEVEL7		3.74		V

The total LCD current is given by Equation 3.3 (p. 53). I_{LCDBOOST} is zero if internal boost is off.

Total LCD Current Based on Operational Mode and Internal Boost

 $I_{LCDTOTAL} = I_{LCD} + I_{LCDBOOST}$

(3.3)

3.17 I2C

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		100 ¹	kHz
t _{LOW}	SCL clock low time	4.7			μs
t _{HIGH}	SCL clock high time	4.0			μs
t _{SU,DAT}	SDA set-up time	250			ns
t _{HD,DAT}	SDA hold time	8		3450 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	4.7			μs
t _{HD,STA}	(Repeated) START condition hold time	4.0			μs
t _{SU,STO}	STOP condition set-up time	4.0			μs
t _{BUF}	Bus free time between a STOP and a START condi- tion	4.7			μs

¹For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32WG Reference Manual. ²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}). ³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 4).

Table 3.27. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			μs
t _{HIGH}	SCL clock high time	0.6			μs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			μs
t _{HD,STA}	(Repeated) START condition hold time	0.6			μs
t _{SU,STO}	STOP condition set-up time	0.6			μs
t _{BUF}	Bus free time between a STOP and a START condi- tion	1.3			μs

¹For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32WG Reference Manual. ²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 4).



Symbol	Parameter	Min	Тур	Max	Unit
t _{SCLK_hi} 12	SCLK high period	3 * t _{HFPER-} CLK			ns
t _{SCLK_lo} ¹²	SCLK low period	3 * t _{HFPER-} CLK			ns
t _{CS_ACT_MI} ¹²	CS active to MISO	5.00		35.00	ns
t _{CS_DIS_MI} ¹²	CS disable to MISO	5.00		35.00	ns
t _{SU_MO} ¹²	MOSI setup time	5.00			ns
t _{H_MO} ¹²	MOSI hold time	2 + 2 * t _{HF-} PERCLK			ns
t _{SCLK_MI} ¹²	SCLK to MISO	-264 + t _{HF-} PERCLK		-234 + 2 * t _{HFPERCLK}	ns

Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

 $^2\text{Measurement}$ done at 10% and 90% of V_{DD} (figure shows 50% of $_{\text{VDD}})$

3.19 Digital Peripherals

Table 3.33. Digital Peripherals

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
I _{USART}	USART current	USART idle current, clock en- abled		4.0		μΑ/ MHz
I _{UART}	UART current	UART idle current, clock en- abled		3.8		μΑ/ MHz
I _{LEUART}	LEUART current	LEUART idle current, clock en- abled		194.0		nA
I _{I2C}	I2C current	I2C idle current, clock enabled		7.6		μΑ/ MHz
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.5		μΑ/ MHz
I _{LETIMER}	LETIMER current	LETIMER idle current, clock enabled	85.8			nA
I _{PCNT}	PCNT current	PCNT idle current, clock en- abled	g			nA
I _{RTC}	RTC current	RTC idle current, clock enabled		54.6		nA
I _{LCD}	LCD current	LCD idle current, clock enabled		72.7		nA
I _{AES}	AES current	AES idle current, clock enabled		1.8		μΑ/ MHz
I _{GPIO}	GPIO current	GPIO idle current, clock en- abled		3.4		μΑ/ MHz
I _{EBI}	EBI current	EBI idle current, clock enabled	6.5			μΑ/ MHz
I _{PRS}	PRS current	PRS idle current	3.9			μΑ/ MHz
I _{DMA}	DMA current	Clock enable			μΑ/ MHz	

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32WG890.

4.1 Pinout

The *EFM32WG890* pinout is shown in Figure 4.1 (p. 58) and Table 4.1 (p. 58). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32WG890 Pinout (top view, not to scale)

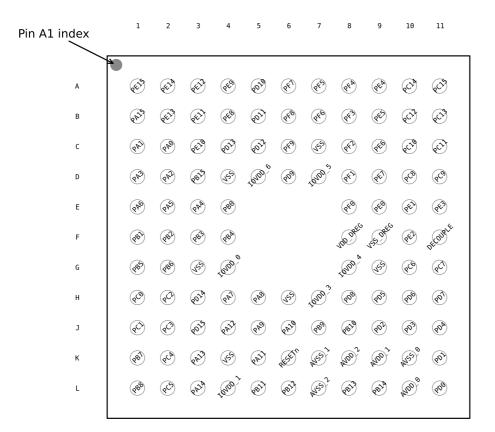


Table 4.1. Device Pinout

	GA112 Pin# and Name	Pin Alternate Functionality / Description						
Pin #	Pin Name	Analog EBI		Timers	Communication	Other		
A1	PE15	LCD_SEG11	EBI_AD07 #0/1/2	TIM3_CC1 #0	LEU0_RX #2			
A2	PE14	LCD_SEG10	EBI_AD06 #0/1/2	TIM3_CC0 #0	LEU0_TX #2			
A3	PE12	LCD_SEG8	EBI_AD04 #0/1/2	TIM1_CC2 #1	US0_RX #3 US0_CLK #0 I2C0_SDA #6	CMU_CLK1 #2 LES_ALTEX6 #0		



	GA112 Pin# and Name	# Pin Alternate Functionality / Description								
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other				
K5	PA11	LCD_SEG39	EBI_HSNC #0/1/2							
K6	RESETn	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.								
K7	AVSS_1	Analog ground 1.								
K8	AVDD_2	Analog power supply 2.								
К9	AVDD_1	Analog power supply 1.								
K10	AVSS_0	Analog ground 0.								
K11	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT		TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2				
L1	PB8	LFXTAL_N		TIM1_CC1 #3	US0_RX #4 US1_CS #0					
L2	PC5	ACMP0_CH5 DAC0_N0 / OPAMP_N0	EBI_NANDWEn #0/1/2	LETIM0_OUT1 #3 PCNT1_S1IN #0	US2_CS #0 I2C1_SCL #0	LES_CH5 #0				
L3	PA14	LCD_BEXT	EBI_A02 #0/1/2	TIM2_CC2 #1						
L4	IOVDD_1	Digital IO power supply	1.		1	J				
L5	PB11	DAC0_OUT0 / OPAMP_OUT0		TIM1_CC2 #3 LETIM0_OUT0 #1	I2C1_SDA #1					
L6	PB12	DAC0_OUT1 / OPAMP_OUT1		LETIM0_OUT1 #1	I2C1_SCL #1					
L7	AVSS_2	Analog ground 2.								
L8	PB13	HFXTAL_P			US0_CLK #4/5 LEU0_TX #1					
L9	PB14	HFXTAL_N			US0_CS #4/5 LEU0_RX #1					
L10	AVDD_0	Analog power supply 0.								
L11	PD0	ADC0_CH0 DAC0_OUT0ALT #4/ OPAMP_OUT0ALT OPAMP_OUT2 #1		PCNT2_S0IN #0	US1_TX #1					

4.2 Alternate Functionality Pinout

A wide selection of alternate functionality is available for multiplexing to various pins. This is shown in Table 4.2 (p. 62). The table shows the name of the alternate functionality in the first column, followed by columns showing the possible LOCATION bitfield settings.

Note

Some functionality, such as analog interfaces, do not have alternate settings or a LOCA-TION bitfield. In these cases, the pinout is shown in the column corresponding to LOCA-TION 0.

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
ACMP0_CH0	PC0							Analog comparator ACMP0, channel 0.
ACMP0_CH1	PC1							Analog comparator ACMP0, channel 1.



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Alternate			L	OCATIO	N			
Functionality	0	1	2	3	4	5	6	Description
OPAMP_OUT2	PD5	PD0						Operational Amplifier 2 output.
DAC0_P0 / OPAMP_P0	PC4							Operational Amplifier 0 external positive input.
DAC0_P1 / OPAMP_P1	PD6							Operational Amplifier 1 external positive input.
OPAMP_P2	PD4							Operational Amplifier 2 external positive input.
								Debug-interface Serial Wire clock input.
DBG_SWCLK	PF0	PF0	PF0	PF0				Note that this function is enabled to pin out of reset, and has a built-in pull down.
								Debug-interface Serial Wire data input / output.
DBG_SWDIO	PF1	PF1	PF1	PF1				Note that this function is enabled to pin out of reset, and has a built-in pull up.
								Debug-interface Serial Wire viewer Output.
DBG_SWO	PF2	PC15	PD1	PD2				Note that this function is not enabled after reset, and must be enabled by software to be used.
EBI_A00	PA12	PA12	PA12					External Bus Interface (EBI) address output pin 00.
EBI_A01	PA13	PA13	PA13					External Bus Interface (EBI) address output pin 01.
EBI_A02	PA14	PA14	PA14					External Bus Interface (EBI) address output pin 02.
EBI_A03	PB9	PB9	PB9					External Bus Interface (EBI) address output pin 03.
EBI_A04	PB10	PB10	PB10					External Bus Interface (EBI) address output pin 04.
EBI_A05	PC6	PC6	PC6					External Bus Interface (EBI) address output pin 05.
EBI_A06	PC7	PC7	PC7					External Bus Interface (EBI) address output pin 06.
EBI_A07	PE0	PE0	PE0					External Bus Interface (EBI) address output pin 07.
EBI_A08	PE1	PE1	PE1					External Bus Interface (EBI) address output pin 08.
EBI_A09	PE2	PC9	PC9					External Bus Interface (EBI) address output pin 09.
EBI_A10	PE3	PC10	PC10					External Bus Interface (EBI) address output pin 10.
EBI_A11	PE4	PE4	PE4					External Bus Interface (EBI) address output pin 11.
EBI_A12	PE5	PE5	PE5					External Bus Interface (EBI) address output pin 12.
EBI_A13	PE6	PE6	PE6					External Bus Interface (EBI) address output pin 13.
EBI_A14	PE7	PE7	PE7					External Bus Interface (EBI) address output pin 14.
EBI_A15	PC8	PC8	PC8					External Bus Interface (EBI) address output pin 15.
EBI_A16	PB0	PB0	PB0					External Bus Interface (EBI) address output pin 16.
EBI_A17	PB1	PB1	PB1					External Bus Interface (EBI) address output pin 17.
EBI_A18	PB2	PB2	PB2					External Bus Interface (EBI) address output pin 18.
EBI_A19	PB3	PB3	PB3					External Bus Interface (EBI) address output pin 19.
EBI_A20	PB4	PB4	PB4					External Bus Interface (EBI) address output pin 20.
EBI_A21	PB5	PB5	PB5					External Bus Interface (EBI) address output pin 21.
EBI_A22	PB6	PB6	PB6					External Bus Interface (EBI) address output pin 22.
EBI_A23	PC0	PC0	PC0					External Bus Interface (EBI) address output pin 23.
EBI_A24	PC1	PC1	PC1					External Bus Interface (EBI) address output pin 24.
EBI_A25	PC2	PC2	PC2					External Bus Interface (EBI) address output pin 25.
EBI_A26	PC4	PC4	PC4					External Bus Interface (EBI) address output pin 26.
EBI_A27	PD2	PD2	PD2					External Bus Interface (EBI) address output pin 27.
EBI_AD00	PE8	PE8	PE8					External Bus Interface (EBI) address and data input / output pin 00.



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Alternate			L	OCATIO	DN			
Functionality	0	1	2	3	4	5	6	Description
LCD_SEG34	PB2							LCD segment line 34. Segments 32, 33, 34 and 35 are con- trolled by SEGEN8.
LCD_SEG35	PA7							LCD segment line 35. Segments 32, 33, 34 and 35 are con- trolled by SEGEN8.
LCD_SEG36	PA8							LCD segment line 36. Segments 36, 37, 38 and 39 are con- trolled by SEGEN9.
LCD_SEG37	PA9							LCD segment line 37. Segments 36, 37, 38 and 39 are con- trolled by SEGEN9.
LCD_SEG38	PA10							LCD segment line 38. Segments 36, 37, 38 and 39 are con- trolled by SEGEN9.
LCD_SEG39	PA11							LCD segment line 39. Segments 36, 37, 38 and 39 are con- trolled by SEGEN9.
LES_ALTEX0	PD6							LESENSE alternate exite output 0.
LES_ALTEX1	PD7							LESENSE alternate exite output 1.
LES_ALTEX2	PA3							LESENSE alternate exite output 2.
LES_ALTEX3	PA4							LESENSE alternate exite output 3.
LES_ALTEX4	PA5							LESENSE alternate exite output 4.
LES_ALTEX5	PE11							LESENSE alternate exite output 5.
LES_ALTEX6	PE12							LESENSE alternate exite output 6.
LES_ALTEX7	PE13							LESENSE alternate exite output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH2	PC2							LESENSE channel 2.
LES_CH3	PC3							LESENSE channel 3.
LES_CH4	PC4							LESENSE channel 4.
LES_CH5	PC5							LESENSE channel 5.
LES_CH6	PC6							LESENSE channel 6.
LES_CH7	PC7							LESENSE channel 7.
LES CH8	PC8							LESENSE channel 8.
LES_CH9	PC9							LESENSE channel 9.
LES_CH10	PC10							LESENSE channel 10.
	PC10							LESENSE channel 11.
LES_CH11								
LES_CH12	PC12							LESENSE channel 12.
LES_CH13	PC13							LESENSE channel 13.
LES_CH14	PC14							LESENSE channel 14.
LES_CH15	PC15							LESENSE channel 15.
LETIM0_OUT0	PD6	PB11	PF0	PC4				Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7	PB12	PF1	PC5				Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14	PE15	PF1	PA0			LEUART0 Receive input.
LEU0_TX	PD4	PB13	PE14	PF0	PF2			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LEU1_RX	PC7	PA6						LEUART1 Receive input.
LEU1_TX	PC6	PA5						LEUART1 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8							Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.

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